

MULTI-RESISTIVE STATE MATERIAL THAT USES DOPANTS

Abstract

A multi-resistive state material that uses dopants is provided. A multi-resistive state material can be used in a memory cell to store information. However, a multi-resistive state material may not have electrical properties that are appropriate for a memory device. Intentionally doping a multi-resistive state material to modify the electrical properties can, therefore, be desirable.